

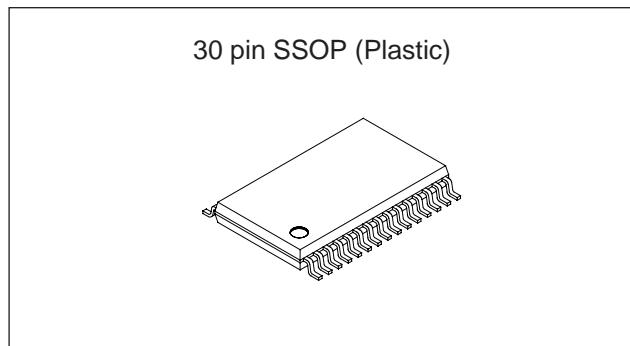
RF Signal Processor for CD Players

Description

The CXA2581N is an RF signal processing IC for compact disc players.

Features

- Wide band RF signal processing
- RF system VCA circuit
- RF system equalizer (supports CAV mode)
- Supports pickups with built-in RF summing amplifier
- Low current consumption mode (EQ Pass mode)
- RW/ROM switching mode
- Center error amplifier
- Output DC level shift circuit
- TE balance adjustment function



Absolute Maximum Ratings

• Supply voltage	V _{CC}	7	V
• Storage temperature	T _{STG}	-65 to +150	°C
• Allowable power dissipation	P _D	620	mW

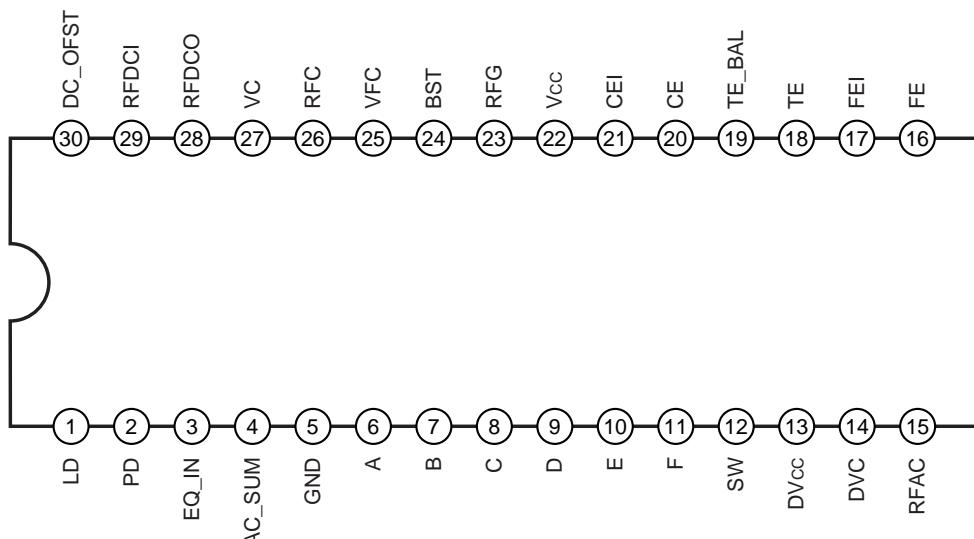
Functions

- RF AC summing amplifier, equalizer, VCA
- RF DC summing amplifier
- Focus error amplifier
- Tracking error amplifier
- Center error amplifier
- Automatic power control
- VC buffer amplifier (analog block, digital block)

Operating Conditions

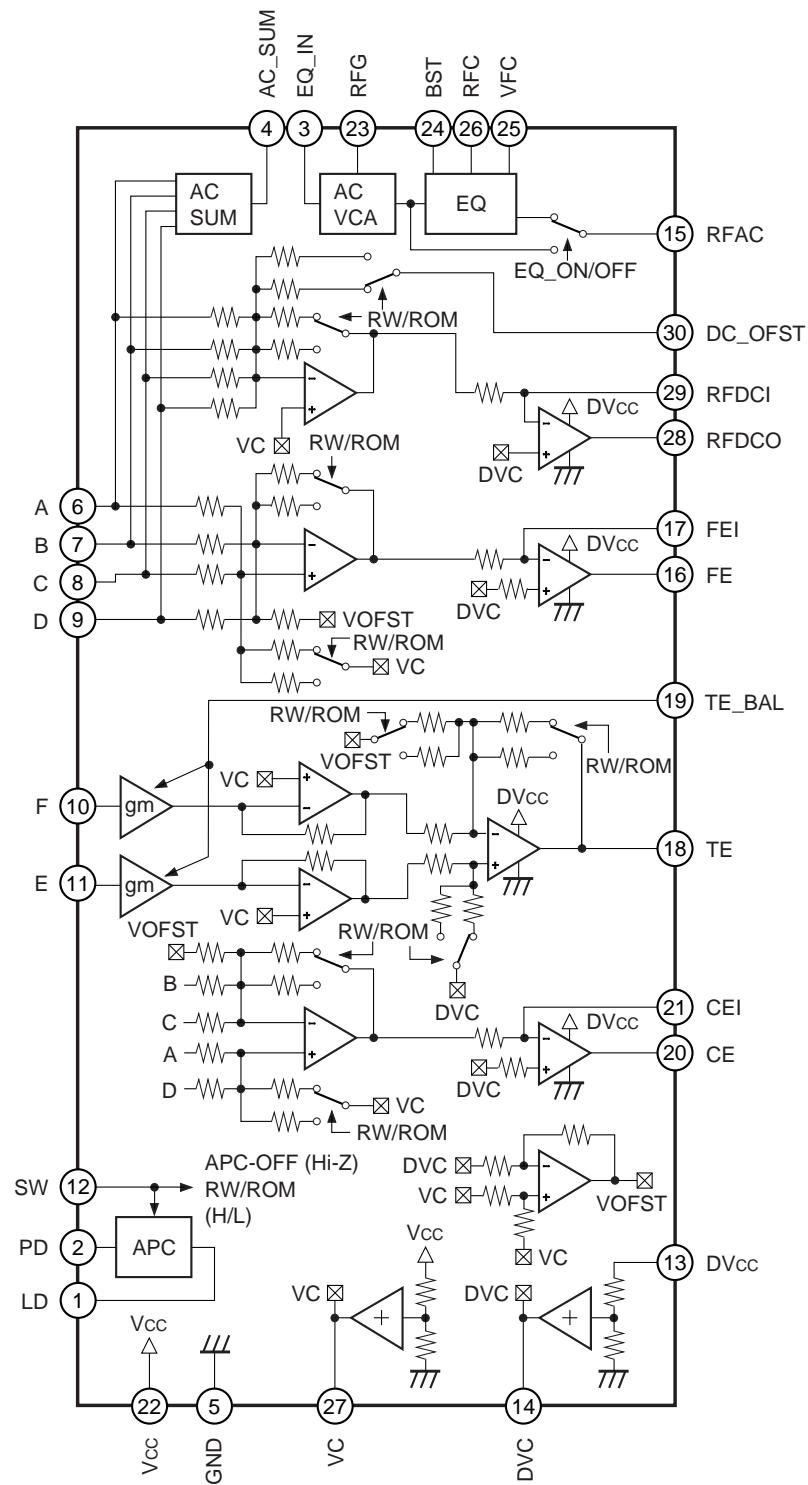
- Operating supply voltage range
V_{CC} – GND 3.4 to 5.5 V
(0V ≤ V_{CC} – DV_{CC} < 2V)
- Note) Care should be taken for the operating voltage.
See page 18.
- Operating temperature T_{OPR} -30 to +85 °C

Pin Configuration



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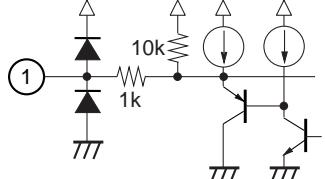
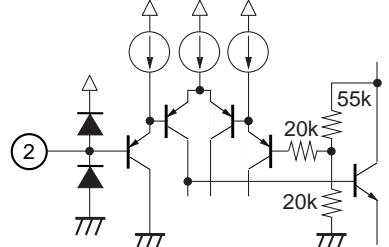
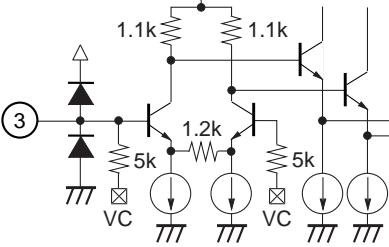
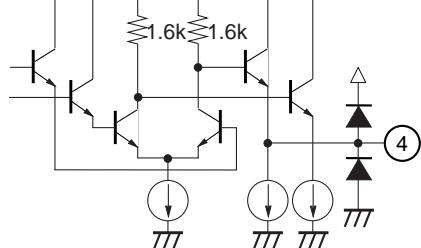
Block Diagram

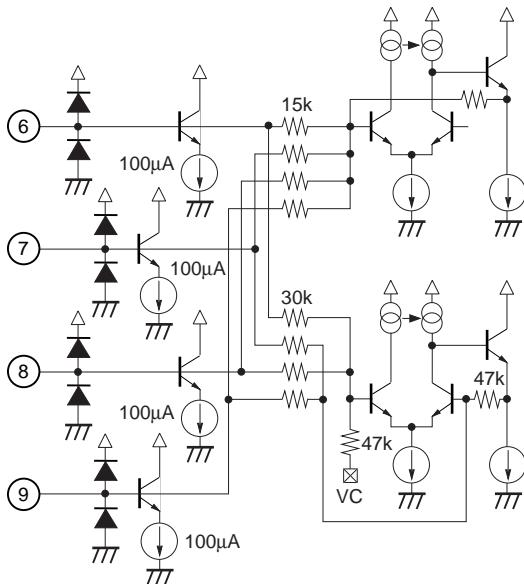
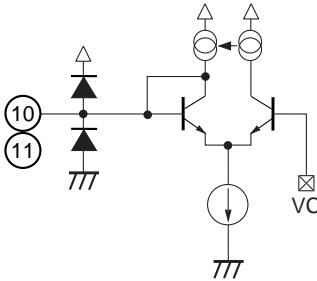
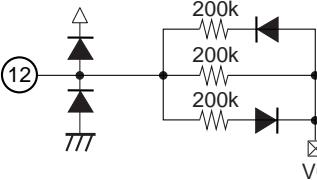
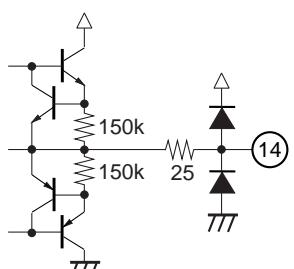


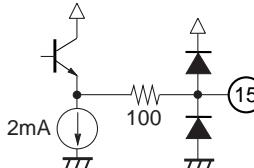
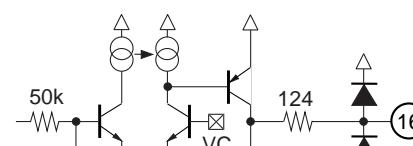
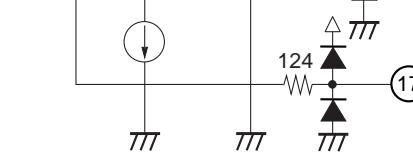
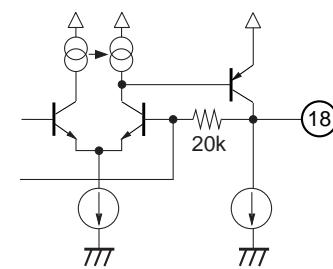
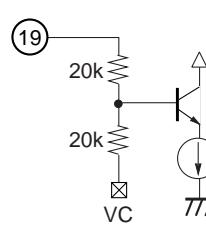
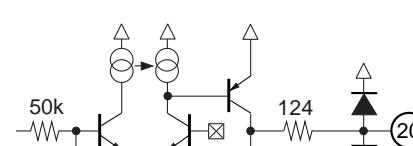
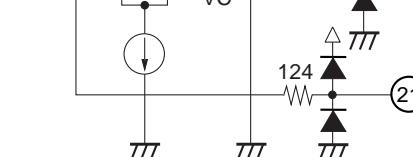
Pin Description

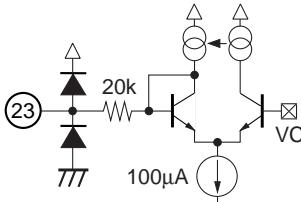
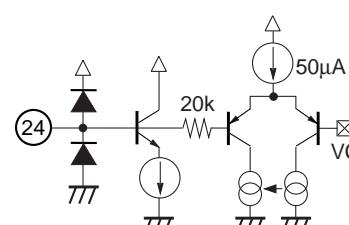
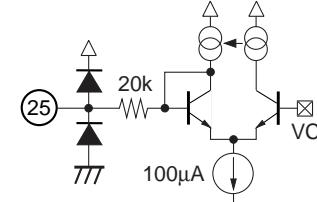
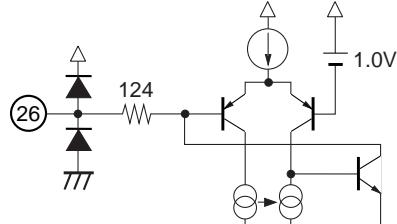
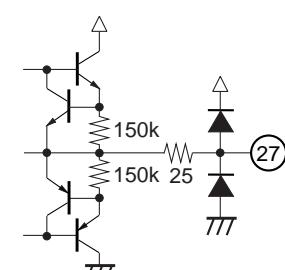
Pin No.	Symbol	I/O	Description
1	LD	O	APC amplifier output.
2	PD	I	APC amplifier input.
3	EQ_IN	I	RFAC system VCA block and EQ block input.
4	AC_SUM	O	RFAC system RF SUM output.
5	GND	I	GND.
6	A	I	A signal input.
7	B	I	B signal input.
8	C	I	C signal input.
9	D	I	D signal input.
10	E	I	E signal input.
11	F	I	F signal input.
12	SW	I	Mode switching signal input.
13	DVcc	I	DVcc.
14	DVC	O	DVC output.
15	RFAC	O	RFAC signal output.
16	FE	O	Focus error signal output.
17	FEI	I	FE amplifier virtual ground.
18	TE	O	Tracking error signal output.
19	TE_BAL	I	TE balance adjustment.
20	CE	O	Center error signal output.
21	CEI	I	CE amplifier virtual ground.
22	Vcc	I	Vcc.
23	RFG	I	RFAC system VCA block low frequency gain adjustment.
24	BST	I	EQ boost level adjustment.
25	VFC	I	EQ cut-off frequency adjustment.
26	RFC	I	EQ cut-off frequency adjustment.
27	VC	O	VC voltage output.
28	RFDCO	O	RFDC signal output.
29	RFDCI	I	RFDC amplifier virtual ground.
30	DC_OFST	I	RFDC signal output offset adjustment.

Pin Description

Pin No.	Symbol	I/O	Equivalent circuit	Description
1	LD	O		APC amplifier output.
2	PD	I		APC amplifier input.
3	EQ_IN	I		Equalizer circuit input.
4	AC_SUM	O		RFAC summing amplifier output.
5	GND	—	—	GND.

Pin No.	Symbol	I/O	Equivalent circuit	Description
6	A	I		RF summing amplifier and focus error amplifier input.
7	B	I		Tracking error amplifier input.
8	C	I		
9	D	I		CD-ROM/RW switching input. RW when connected to Vcc, ROM when connected to GND.
10	E	I		Digital power supply.
11	F	I		(DVcc + GND)/2 voltage output.

Pin No.	Symbol	I/O	Equivalent circuit	Description
15	RFAC	O		RFAC amplifier output.
16	FE	O		Focus error amplifier output.
17	FEI	I		Focus error amplifier gain adjustment. The gain is adjusted by the external resistance value connected between this pin and Pin 16.
18	TE	O		Tracking error amplifier output.
19	TE_BAL	I		Tracking error E and F gain balance adjustment.
20	CE	O		Center error amplifier output.
21	CEI	I		Center error amplifier gain adjustment. The gain is adjusted by the external resistance value connected between this pin and Pin 20.

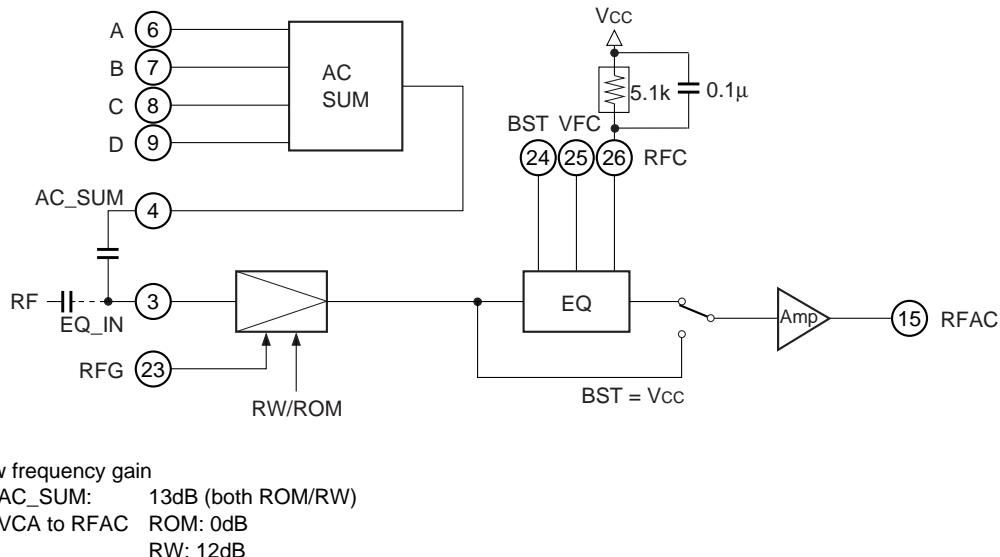
Pin No.	Symbol	I/O	Equivalent circuit	Description
22	Vcc	—	—	Vcc. (AVcc)
23	RFG	I		Sets the RFAC low frequency gain.
24	BST	I		Input for adjusting the equalizer circuit boost level.
25	VFC	I		Input for adjusting the equalizer circuit boost frequency with the control voltage.
26	RFC	I		Input for adjusting the equalizer circuit boost frequency with external resistance.
27	VC	O		(Vcc + GND)/2 voltage output.

Pin No.	Symbol	I/O	Equivalent circuit	Description
28	RFDC	O		RFDC amplifier output.
29	RFDCI	I		RFDC amplifier gain adjustment. The gain is adjusted by the external resistance value connected between this pin and Pin 28.
30	DC_OFST	I		RFDC amplifier offset control.

Description of Functions

• RFAC

The RF signal input by connecting capacitance to the EQ_IN pin is equalized, arithmetically amplified and then output from the RFAC pin.



The EQ can be bypassed by connecting the BST control pin (Pin 24) to Vcc.

In this case only the EQ block enters sleep mode and low power consumption mode (slim mode) is activated.
 The low frequency gain is the same value as for EQ ON mode.

If RF (summing signal) is present at the pickup output pin, input the addition output signal to EQ_IN (Pin 3) coupled by capacitance.

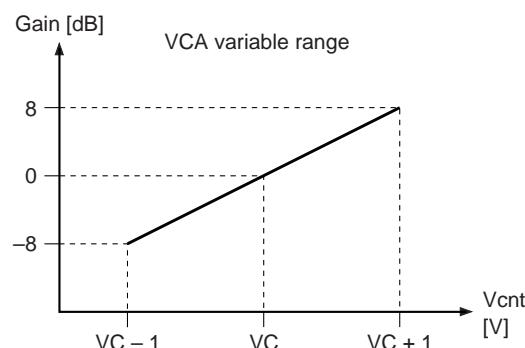
When using a pickup without a summing output function, perform addition with the AC SUM block and then input the signal to EQ_IN (Pin 3) coupled by capacitance.

RW/ROM switching is done by the VCA block, so either input method can be used without problem.

The RW gain is 12dB higher than the ROM gain.

The VCA low frequency gain can be adjusted by the RFG (Pin 23) voltage.

The control voltage vs. low frequency gain characteristics are shown in the graph to the right.

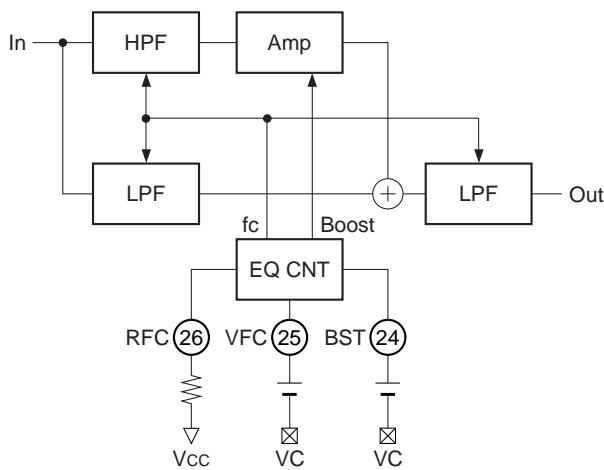


The RFAC pin (Pin 15) is an NPN transistor emitter follower output.

The maximum drive current is approximately 2mA.

If the load capacitance distorts the output waveform, connect resistance between Pin 15 and GND to increase the drive current.

- EQ



The diagram to the left shows the EQ internal block diagram.

The EQ consists of a combination of HPF and LPF. The HPF and LPF transmittance is the Bessel function. The boost gain can be adjusted by adjusting the HPF gain.

The boost frequency is adjusted by the RFC external resistance value and the VFC control voltage value.

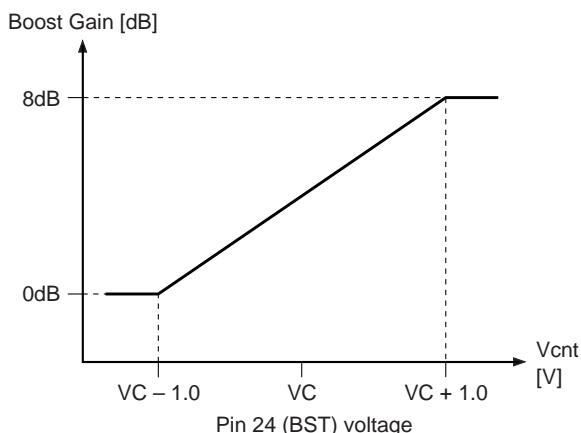
RFC resistance value: The cut-off frequency f_o of each filter is adjusted by the Pin 26 external resistance value.

The VFC voltage can be varied using this f_o as the reference.

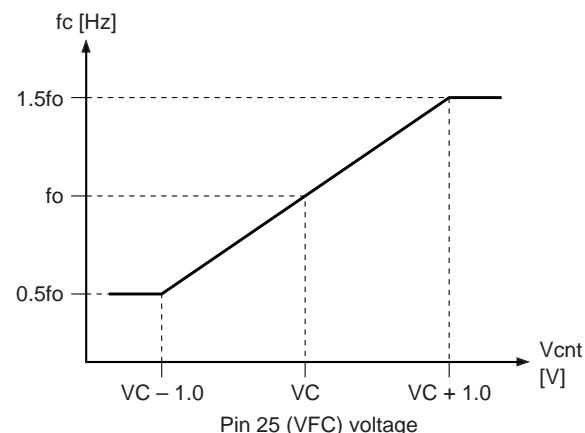
VFC voltage: f_o can be changed by the voltage applied to Pin 25.

The boost gain can be adjusted by the BST pin control voltage.

The control characteristics are shown in the graph below.

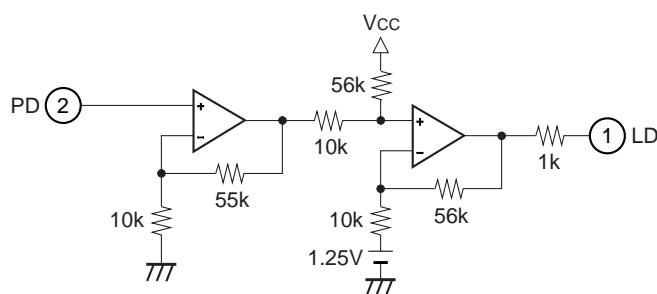


The cut-off frequency control characteristics are shown in the graph below.



- APC (Automatic Power Control)

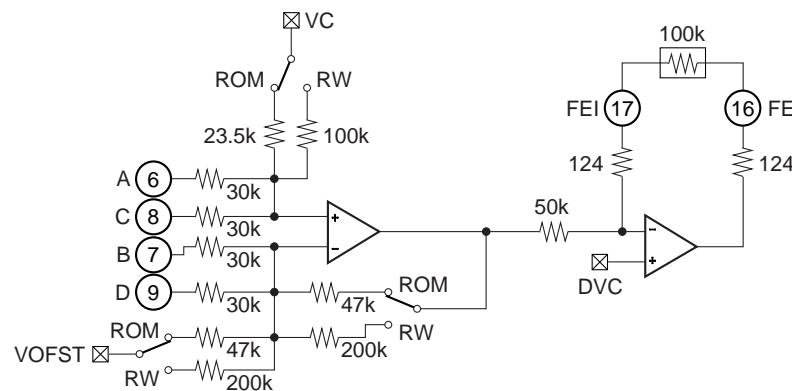
When the laser diode is driven by a constant current, the optical power output has extremely large negative temperature characteristics. Therefore, the current must be controlled to maintain the monitor photo diode output at a constant level. This control is performed by the APC function.



- Focus Error

The signals input to the A and C pins and the B and D pins are arithmetically amplified and the focus error signal is output.

This circuit has RW/ROM switching and offset addition functions.



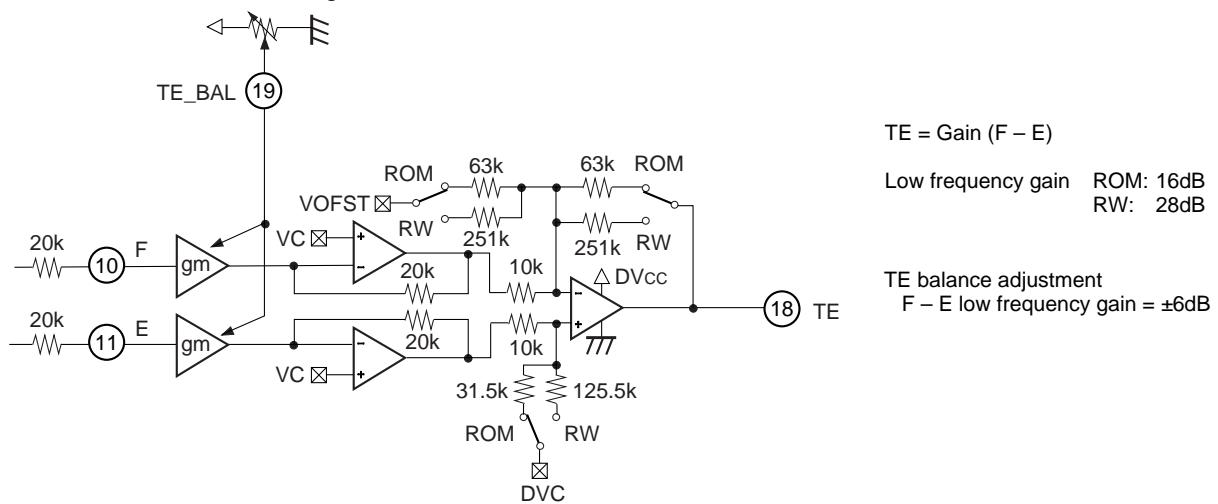
$$\text{FE} = \text{Gain} \{ (B + D) - (A + C) \}$$

Low frequency gain ROM: 16dB
 RW: 28dB

Cut-off frequency f_c (typ.) ROM: 300kHz
 RW: 300kHz

- Tracking Error

The signals input to the E and F pins are arithmetically amplified and the tracking error signal is output.
This circuit has RW/ROM switching and offset addition functions.

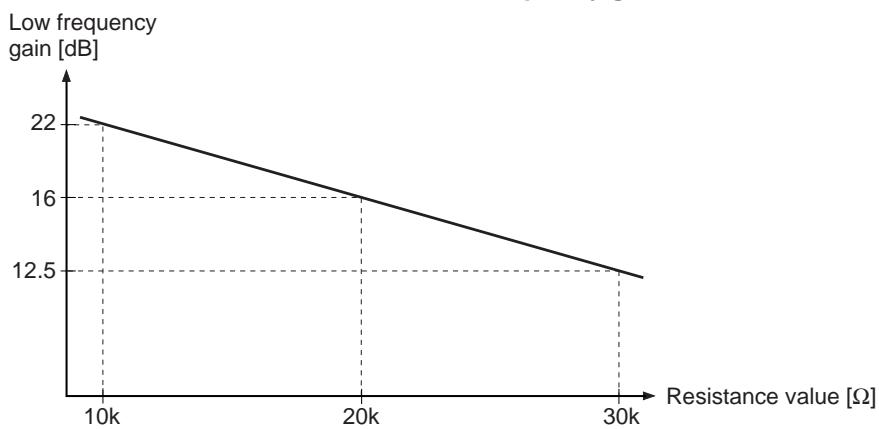


$$\text{TE} = \text{Gain} (F - E)$$

Low frequency gain ROM: 16dB
 RW: 28dB

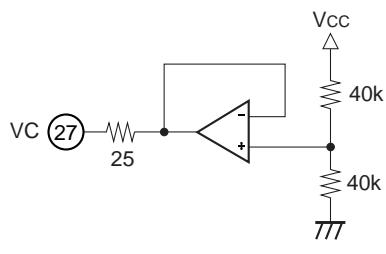
TE balance adjustment
F - E low frequency gain = ± 6 dB

External resistance value vs. Low frequency gain



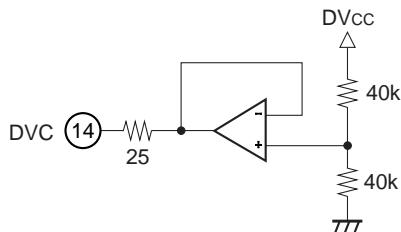
• VC Buffer

This outputs the VC ($(1/2) V_{cc}$) voltage.
 The maximum output current is approximately $\pm 3\text{mA}$.
 Use this voltage as the analog block VC voltage.



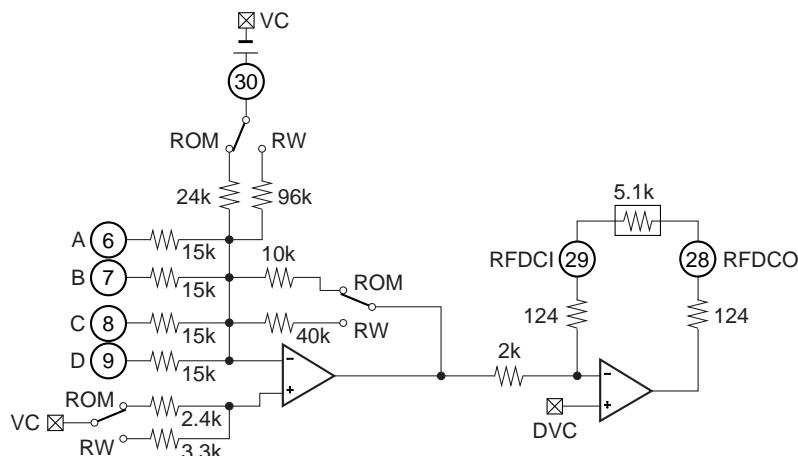
• DVC Buffer

This outputs the $1/2 DV_{cc}$ voltage.
 The maximum output current is approximately $\pm 3\text{mA}$.
 Use this voltage as the digital block VC voltage.
 The output DC voltage of each block is level shifted using the DVC voltage as the reference.



• RFDC

The signals input to the A, B, C and D pins are added, amplified and the RFDC signal is output. RW/ROM switching and low frequency gain adjustment are possible.



$$RFDC = \text{Gain} (A + B + C + D)$$

Low frequency gain ROM: 17.5dB

 RW: 29.5dB

f_c (Typ)

 ROM: 20MHz

 RW: 5MHz

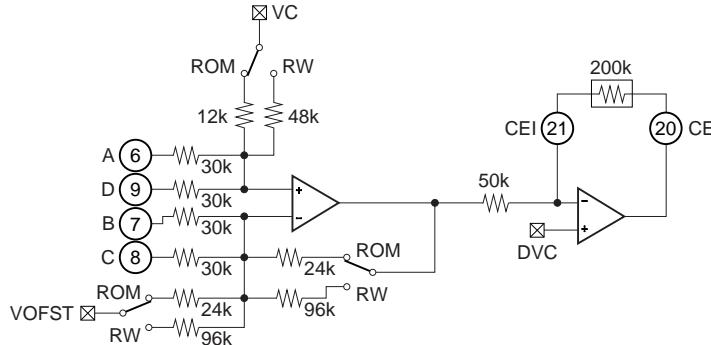
The gain can be adjusted by the external resistance connected between Pins 28 and 29.

The output voltage offset can be adjusted by controlling the Pin 30 voltage.

• Center Error

The signals input to the A and D pins and the B and C pins are arithmetically amplified and the center error signal is output.

RW/ROM switching, low frequency gain adjustment and offset adjustment are possible.



The $(B + C) - (A + D)$ signal is arithmetically amplified.

Low frequency gain ROM: 16dB
 RW: 28dB

Cut-off frequency f_c (typ.)

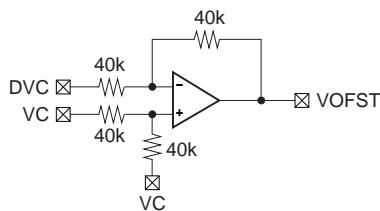
ROM: 200kHz
RW: 200kHz

• Output Offset Shift

The RFDC, FE, TE and CE output DC voltages are level shifted to the digital VC voltage (DVC).

The reference voltage of this IC is the VC voltage, and only the output reference voltage changes.

The maximum output voltage of each output signal should be kept to the digital Vcc voltage (DVcc) or less in order to protect the DSP_IC.



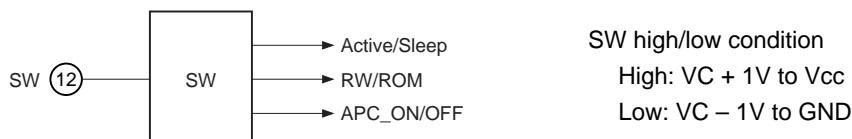
The VC and DVC voltages are arithmetically amplified and output as the VOFST voltage.

The VOFST voltage serves as the level shift reference voltage, and is distributed to each block.

• SW

This controls the laser (APC) on/off, active/sleep mode, and RW/ROM mode switching.

Switching is controlled by the voltage applied to the SW pin.



The VC buffer is always in active mode even if it enters sleep mode.

In the function block, MODE_SW is always set to active mode.

Control voltage \ Item	APC	Active/Sleep	RW/ROM
Vcc	ON	Active	RW
VC or Hi-Z	OFF	Sleep	—
GND	ON	Active	ROM

Electrical Characteristics(V_{CC} = 1.7V, V_{EE} = -1.7V, DV_{CC} = 1.7V, DV_{EE} = -1.7V)

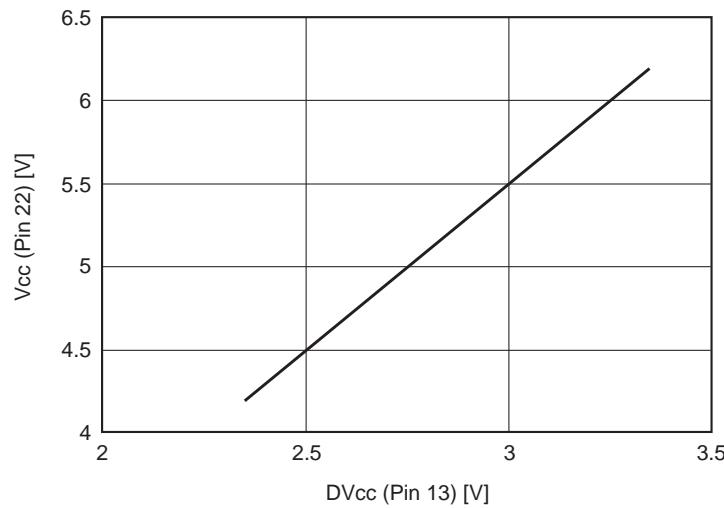
Measure- ment No.	Func- tion	Measurement item	Symbol	Switch conditions						Bias conditions						Measure- ment pin	Measure- ment conditions	Min.	Typ.	Max.	Unit					
				S1	S2	S3	S4	S5	S6	S7	S8	S9	S10	S11	S12	V1 amplitude frequency	E1	E2	E3	E4	E5	E6	E7			
1		Current consumption (Active, EQ On)	Icc_Aeqon									0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	mA			
2		Current consumption (Active, EQ Off)	Icc_Aeqoff													1.7V					22	Pin current	30	50	70	mA
3		Current consumption (DV _{CC})	Icc_Dvcc									0V									13	Pin current	0.2	0.5	0.8	mA
4		Current consumption (Sleep)	Icc_Slp	H-Z																	22	Pin current	3	5	8	mA
5		SUM offset voltage	ACSUM_Ofst																	4	Pin voltage	-1.2	-0.7	-0.2	V	
6		SUM low frequency gain	Gsum	O O O O				0.1Vp-p	100kHz	70mV										4	20 log (V _{out} /V _{in})	11	13	15	dB	
7		SUM frequency response	Fsum	O O O O				0.1Vp-p	10MHz	70mV									4	20 log (V _{out} /V _{in}) - Gsum	-2.5	-0.5	0.5	dB		
8		SUM maximum output voltage H	Vsum_H	O O O O								0.4V								4	Pin voltage -ACSUM_Ofst	1.4	1.6	1.7	V	
9		SUM maximum output voltage L	Vsum_L	O O O O								-0.4V								4	Pin voltage -ACSUM_Ofst	-0.5	-0.3	-0.1	V	
10		Offset Voltage ROM	AC_OfstROM									0V								15	Pin voltage	-0.8	-0.3	0.2	V	
11		Offset voltage RW	AC_OfstRW	O													▼				15	Pin voltage	-0.8	-0.3	0.2	V
12		Low frequency gain ROM_min	Gac_ROM1	O				1.4Vp-p	100kHz	-1.0V										15	20 log (V _{out} /V _{in}) - Gac_ROM1	-11	-8	-5	dB	
13		Low frequency gain ROM_cnt	Gac_ROM2	O				0.8Vp-p	100kHz	0V										15	20 log (V _{out} /V _{in})	-3	0	3	dB	
14		Low frequency gain ROM_max	Gac_ROM3	O				0.3Vp-p	100kHz	1.0V									15	20 log (V _{out} /V _{in}) - Gac_ROM3	5	8	11	dB		
15		Low frequency gain RW_min	Gac_RW1	O				0.35Vp-p	50kHz	-1.0V									15	20 log (V _{out} /V _{in}) - Gac_RW1	-11	-8	-5	dB		
16		Low frequency gain RW_cnt	Gac_RW2	O				0.2Vp-p	50kHz	0V									15	20 log (V _{out} /V _{in}) - Gac_RW2	9	12	15	dB		
17		Low frequency gain RW_max	Gac_RW3	O				0.75mVp-p	50kHz	1.0V	▼								15	20 log (V _{out} /V _{in}) - Gac_RW3	5	8	11	dB		
18		Low frequency gain EQ_off	Gac_EQoff	O				0.8Vp-p	100kHz	0V	1.7V	▼							15	20 log (V _{out} /V _{in})	-2	0	2	dB		
19		Frequency response Min_L	Fac_MinL	O				0.3Vp-p	10MHz	0V	-1.0V								15	20 log (V _{out} /V _{in}) - Fac_MinL	2	5	8	dB		
20		Frequency response Min_H	Fac_MinH	O				0.3Vp-p	30MHz		1.0V	▼							15	20 log (V _{out} /V _{in}) - Fac_MinH	2	5	8	dB		
21		Frequency response EQ_OFF	Fac_EQoff	O				0.3Vp-p	20MHz	▼	1.7V	0V							15	20 log (V _{out} /V _{in}) - EQoff	-0.5	2.5	5.5	dB		
22		Maximum output voltage H	Vac_H	O O								1.2V							15	Pin voltage - AC_OfstROM	0.8	1	1.2	V		
23		Maximum output voltage L	Vac_L	O O								-1.2V	▼	▼	▼	▼	▼	▼	15	Pin voltage - AC_OfstROM	-1.1	-0.9	-0.7	V		

Measure- ment No.	Func- tion	Measurement item	Symbol	Switch conditions												Bias conditions							Measure- ment pin		Measure- ment conditions		Min.	Typ.	Max.	Unit		
				S1	S2	S3	S4	S5	S6	S7	S8	S9	S10	S11	S12	V1 amplitude	V1 frequency	E1	E2	E3	E4	E5	E6	E7	Pin voltage	Pin voltage	Pin voltage	Pin voltage				
24	Offset voltage ROM	DC_OfsROM	DC_OfsROM									0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	0V	-150	0	150	mV			
25	Offset voltage RW	DC_OfsRW	DC_OfsRW		O																					-150	0	150	mV			
26	Low frequency gain ROM	Gdc_ROM	Gdc_ROM	O	O	O	O	50mVp-p	100kHz																	28	20 log (Vout/Vin)	14.5	17.5	20.5	dB	
27	Low frequency gain RW	Gdc_RW	Gdc_RW	O	O	O	O	O	12.5mVp-p	100kHz																28	20 log (Vout/Vin) - Gdc_ROM	10	12	14	dB	
28	Frequency response ROM	Fdc_ROM	Fdc_ROM	O	O	O	O	50mVp-p	20MHz																	28	20 log (Vout/Vin) - Gdc_RW - Gdc_ROM	-3.5	-0.5	0.5	dB	
29	Frequency response RW	Fdc_RW	Fdc_RW	O	O	O	O	O	12.5mVp-p	5MHz	▼															28	20 log (Vout/Vin) - Gdc_ROM	-4.5	-1.5	-0.5	dB	
30	Maximum output voltage H	Vdc_H	Vdc_H	O	O	O	O	O	O	O	O	0.3V													28	Pin voltage	0.6	0.8	1	V		
31	Maximum output voltage L	Vdc_L	Vdc_L	O	O	O	O	O	O	O	O	-0.3V													28	Pin voltage	-1.7	-1.5	-1.3	V		
32	Offset voltage 1	DC_Ofs1	DC_Ofs1									0V													28	Pin voltage	-0.7	-0.6	-0.5	V		
33	Offset voltage ROM	FE_OfsROM	FE_OfsROM																						0V	16	Pin voltage	-150	0	150	mV	
34	Offset voltage RW	FE_OfsRW	FE_OfsRW	O																						0	16	Pin voltage	-150	0	150	mV
35	Low frequency gain ROM1	Gfe_ROM1	Gfe_ROM1	O	O	O	O	0.1Vp-p	1kHz																16	20 log (Vout/Vin)	12.5	15.5	18.5	dB		
36	Low frequency gain ROM2	Gfe_ROM2	Gfe_ROM2	O	O	O	O	0.1Vp-p	1kHz																16	20 log (Vout/Vin)	12.5	15.5	18.5	dB		
37	Low frequency gain RW1	Gfe_RW1	Gfe_RW1	O	O	O	O	O	25mVp-p	1kHz															16	20 log (Vout/Vin) - Gfe_ROM1	10	12	14	dB		
38	Low frequency gain RW2	Gfe_RW2	Gfe_RW2	O	O	O	O	O	25mVp-p	1kHz															16	20 log (Vout/Vin) - Gfe_ROM2	10	12	14	dB		
39	Frequency response ROM1	Ffe_ROM1	Ffe_ROM1	O	O	O	O	0.1Vp-p	300kHz																16	20 log (Vout/Vin) - Gfe_ROM1	-5.5	-2.5	0.5	dB		
40	Frequency response ROM2	Ffe_ROM2	Ffe_ROM2	O	O	O	O	0.1Vp-p	300kHz																16	20 log (Vout/Vin) - Gfe_ROM2	-5.5	-2.5	0.5	dB		
41	Frequency response RW1	Ffe_RW1	Ffe_RW1	O	O	O	O	O	25mVp-p	300kHz															16	20 log (Vout/Vin) - Gfe_ROM1 - Gfe_ROM2	-5.5	-2.5	0.5	dB		
42	Frequency response RW2	Ffe_RW2	Ffe_RW2	O	O	O	O	O	25mVp-p	300kHz	▼														16	20 log (Vout/Vin) - Gfe_ROM1 - Gfe_ROM2	-5.5	-2.5	0.5	dB		
43	Maximum output voltage H	Vfe_H	Vfe_H	O	O	O	O	O	O	O	O	0.3V													16	Pin voltage	1.3	1.5	1.7	V		
44	Maximum output voltage L	Vfe_L	Vfe_L	O	O	O	O	O	O	O	O	0.3V													16	Pin voltage	-1.7	-1.5	-1.3	V		

Measure- ment No.	Func- tion	Measurement item	Symbol	Switch conditions												Bias conditions							Measure- ment pin		Measure- ment conditions		Min.	Typ.	Max.	Unit
				S1	S2	S3	S4	S5	S6	S7	S8	S9	S10	S11	S12	V1 amplitude	V1 frequency	E1	E2	E3	E4	E5	E6	E7						
45	Offset voltage ROM	TE_OffsetROM	TE_OffsetROM													0V	0V	0V	0V	0V	0V	0V	0V	18	Pin voltage	-200	0	200	mV	
46	Offset voltage RW	TE_OffsetRW	TE_OffsetRW													O									18	Pin voltage	-500	0	500	mV
47	Low frequency gain ROM1	Gfe_ROM1	Gfe_ROM1													O	0.1Vp-p	1kHz							18	20 log (Vout/Vin)	13	16	19	dB
48	Low frequency gain ROM2	Gfe_ROM2	Gfe_ROM2													O	0.1Vp-p	1kHz							18	20 log (Vout/Vin)	13	16	19	dB
49	Low frequency gain RW1	Gfe_RW1	Gfe_RW1													O	O	25mVp-p	1kHz						18	20 log (Vout/Vin) - Gfe_ROM1	10	12	14	dB
50	Low frequency gain RW2	Gfe_RW2	Gfe_RW2													O	O	25mVp-p	1kHz						18	20 log (Vout/Vin) - Gfe_ROM2	10	12	14	dB
51	Frequency response ROM1	Ffe_ROM1	Ffe_ROM1													O	0.1Vp-p	100kHz							18	20 log (Vout/Vin) - Gfe_ROM1	-3.2	-1.2	0.8	dB
52	Frequency response ROM2	Ffe_ROM2	Ffe_ROM2													O	0.1Vp-p	100kHz							18	20 log (Vout/Vin) - Gfe_ROM2	-3.2	-1.2	0.8	dB
53	Frequency response RW1	Ffe_RW1	Ffe_RW1													O	O	25mVp-p	100kHz						18	20 log (Vout/Vin) - Gfe_ROM1	-3.5	-1.5	0.5	dB
54	Frequency response RW2	Ffe_RW2	Ffe_RW2													O	O	25mVp-p	100kHz	▼					18	20 log (Vout/Vin) - Gfe_ROM2	-3.5	-1.5	0.5	dB
55	Balance gain 1	Gfe1	Gfe1													O	O	0.1Vp-p	1kHz		1.0V	18	E, F gain difference	4	6	8	dB			
56	Balance gain 2	Gfe2	Gfe2													O	O	0.1Vp-p	1kHz	▼	-1.0V	18	E, F gain difference	-8	-6	-4	dB			
57	Maximum output voltage H	Vfe_H	Vfe_H													O			0V	18	Pin voltage	1.3	1.5	1.7	V					
58	Maximum output voltage L	Vfe_L	Vfe_L													O			0.6V	18	Pin voltage	-1.7	-1.5	-1.3	V					
59	Offset voltage ROM	CE_OffsetROM	CE_OffsetROM													O			0V					20	Pin voltage	-150	0	150	mV	
60	Offset voltage RW	CE_OffsetRW	CE_OffsetRW													O								20	Pin voltage	-150	0	150	mV	
61	Low frequency gain ROM1	Gfe_ROM1	Gfe_ROM1													O	O	0.1Vp-p	1kHz						20	20 log (Vout/Vin)	12.5	15.5	18.5	dB
62	Low frequency gain ROM2	Gfe_ROM2	Gfe_ROM2													O	O	0.1Vp-p	1kHz						20	20 log (Vout/Vin)	12.5	15.5	18.5	dB
63	Low frequency gain RW1	Gfe_RW1	Gfe_RW1													O	O	25mVp-p	1kHz						20	20 log (Vout/Vin) - Gfe_ROM1	10	12	14	dB
64	Low frequency gain RW2	Gfe_RW2	Gfe_RW2													O	O	25mVp-p	1kHz						20	20 log (Vout/Vin) - Gfe_ROM2	10	12	14	dB
65	Frequency response ROM1	Ffe_ROM1	Ffe_ROM1													O	O	0.1Vp-p	200kHz						20	20 log (Vout/Vin) - Gfe_ROM1	-3.8	-2.3	-0.8	dB
66	Frequency response ROM2	Ffe_ROM2	Ffe_ROM2													O	O	0.1Vp-p	200kHz						20	20 log (Vout/Vin) - Gfe_ROM2	-3.8	-2.3	-0.8	dB
67	Frequency response RW1	Ffe_RW1	Ffe_RW1													O	O	25mVp-p	200kHz						20	20 log (Vout/Vin) - Gfe_ROM1	-3.8	-2.3	-0.8	dB
68	Frequency response RW2	Ffe_RW2	Ffe_RW2													O	O	25mVp-p	200kHz	▼					20	20 log (Vout/Vin) - Gfe_ROM2	-3.8	-2.3	-0.8	dB
69	Maximum output voltage H	Vce_H	Vce_H													O	O			0.5V				20	Pin voltage	1.15	1.35	1.55	V	
70	Maximum output voltage L	Vce_L	Vce_L													O	O		0.5V	▼	▼	▼	▼	20	Pin voltage	-1.7	-1.5	-1.3	V	

Measure- ment No.	Func- tion	Measurement item	Symbol	Switch conditions												Bias conditions							Measure- ment pin	Measure- ment conditions	Min.	Typ.	Max.	Unit	
				S1	S2	S3	S4	S5	S6	S7	S8	S9	S10	S11	S12	V1 amplitude	V1 frequency	E1	E2	E3	E4	E5	E6	E7					
71	Output voltage 1	Vapc1	O												0V	0V	0V	0V	0V	0V	0V	0V	0V	1, 2	Input at which output voltage = 0V	0	150	300	mV
72	Output voltage 2	Vapc2	O																					1	Pin voltage	0.5	0.75	1	V
73	Output voltage 3	Vapc3	O																					1	Pin voltage	-1	-0.75	-0.5	V
74	APC OFF voltage	Vapc_off	O																					1	Pin voltage	1.4	1.6	1.7	V
75	Maximum output current	Iapc_max	O	O																				1	Pin voltage	-0.55	-0.15	0.25	V
76	Output voltage	Vavc													O									27	Pin voltage	-100	0	100	mV
77	Output voltage	Vdvc																						14	Pin voltage	-100	0	100	mV

Notes on Supply Voltage



Vcc voltage value at which the waveform is clipped when DVcc is fixed

The voltage difference between Vcc (Pin 22) and DVcc (Pin 13) should be kept to the value shown in the graph above or less.

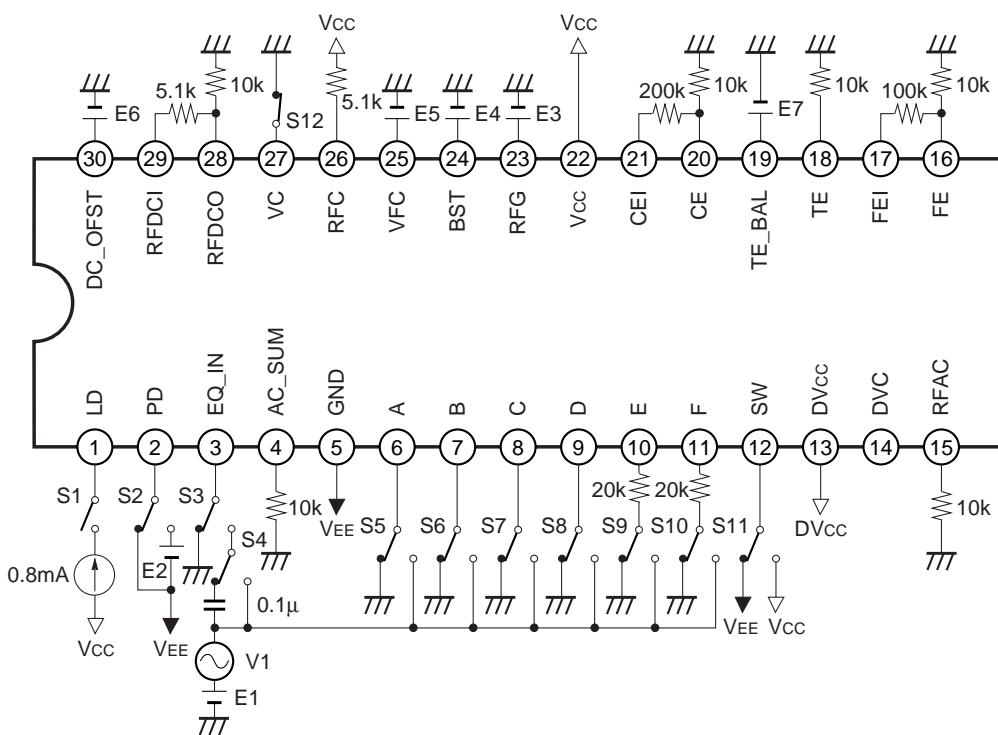
Example) When DVcc = 2.5V

From the graph, Vcc = 4.5V

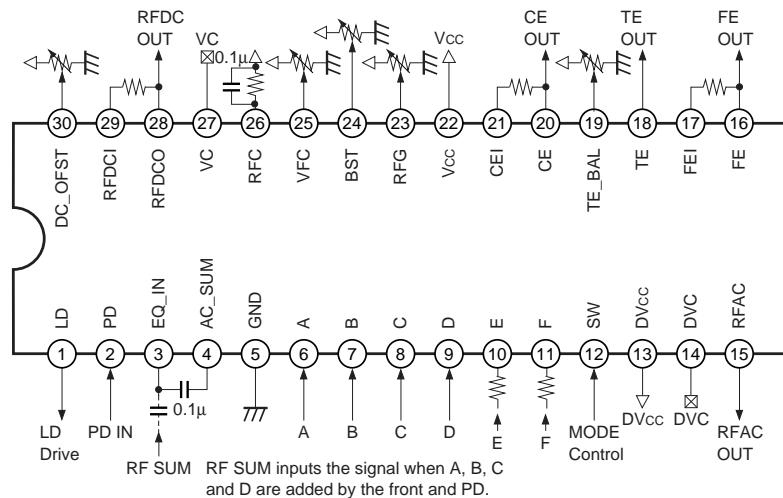
Therefore, Vcc should be from 3.4 to 4.5V.

(3.4V is the minimum operating voltage for the IC.)

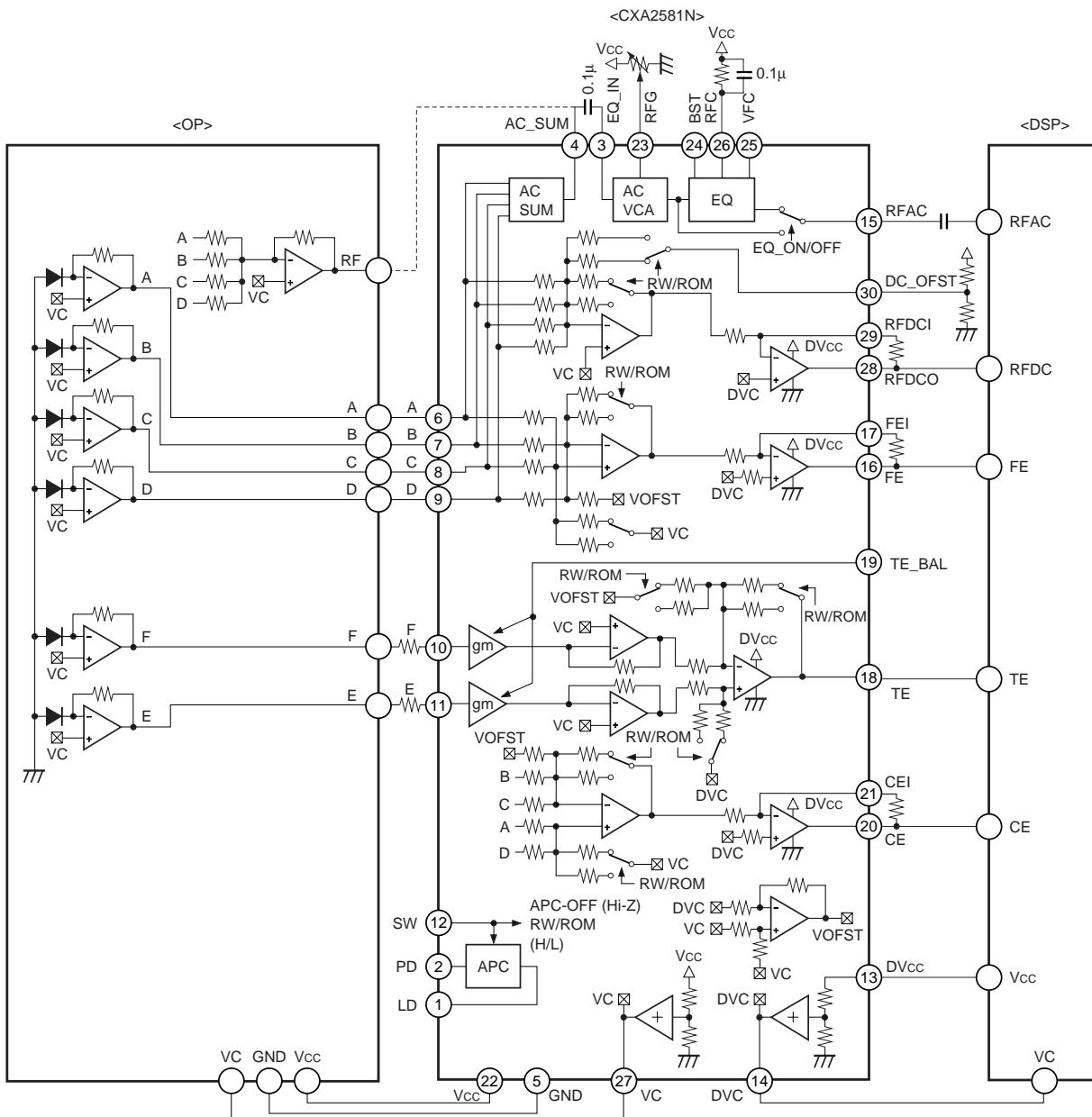
Electrical Characteristics Measurement Circuit



Application Circuits



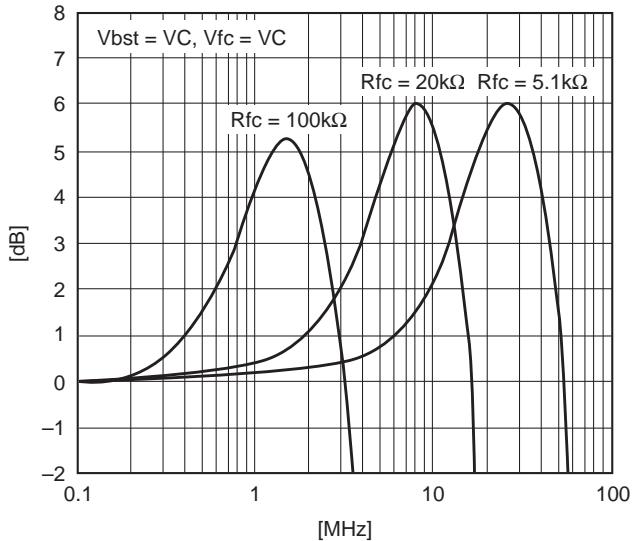
RF-SOM inputs the signal when A, B, and D are added by the front and PD.



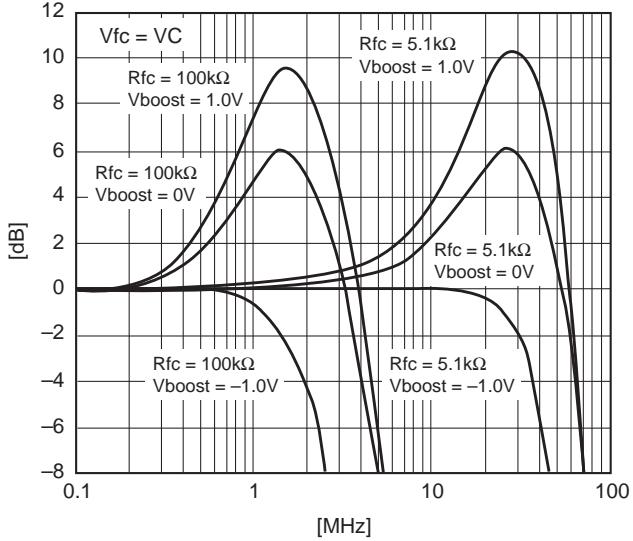
Application circuits shown are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits or for any infringement of third party patent and other right due to same.

Characteristics Graphs

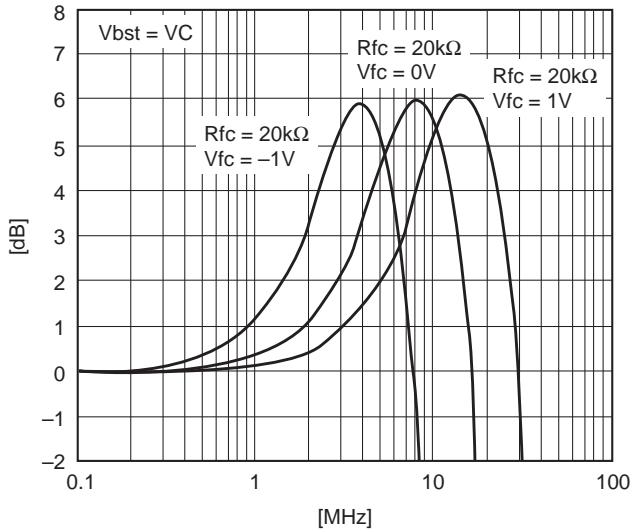
EQ Rfc resistance value vs. Frequency response



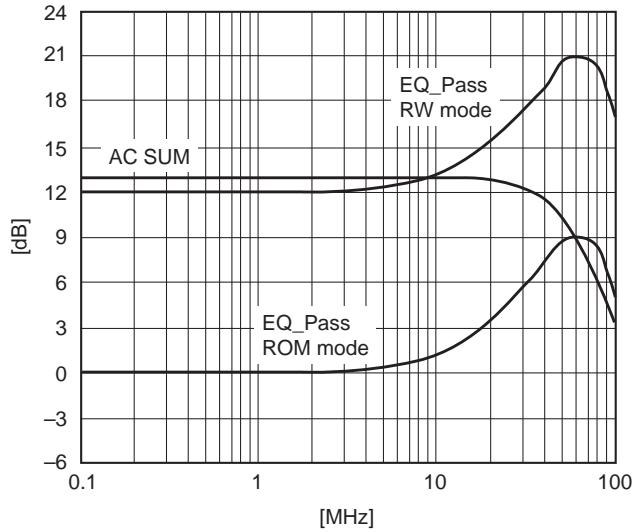
EQ boost voltage vs. Frequency response



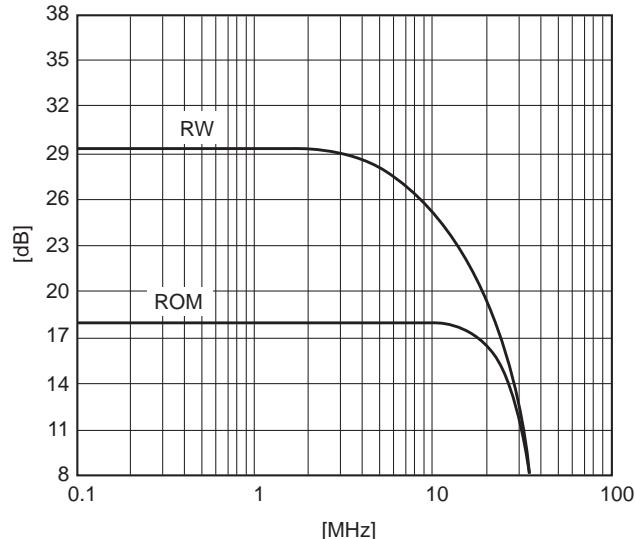
EQ Vfc vs. frequency response



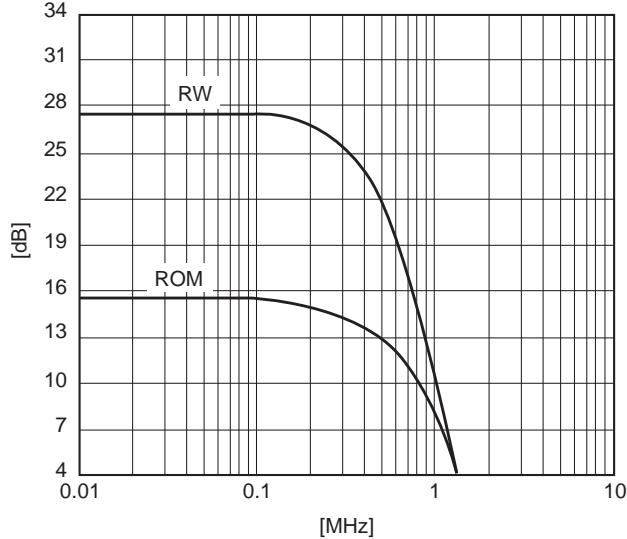
RF AC frequency response

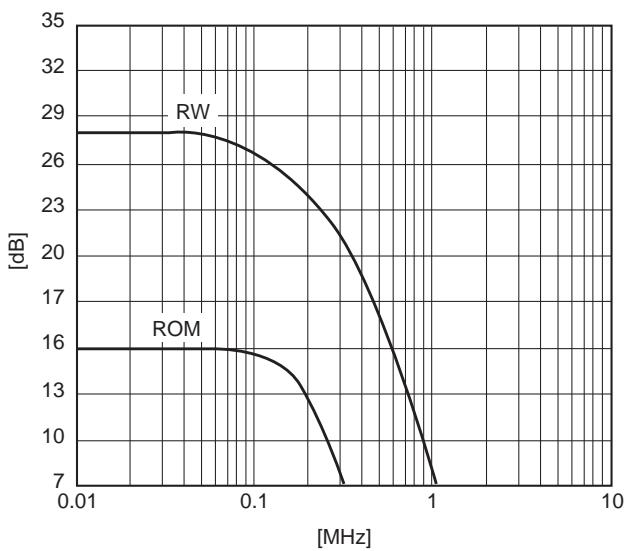
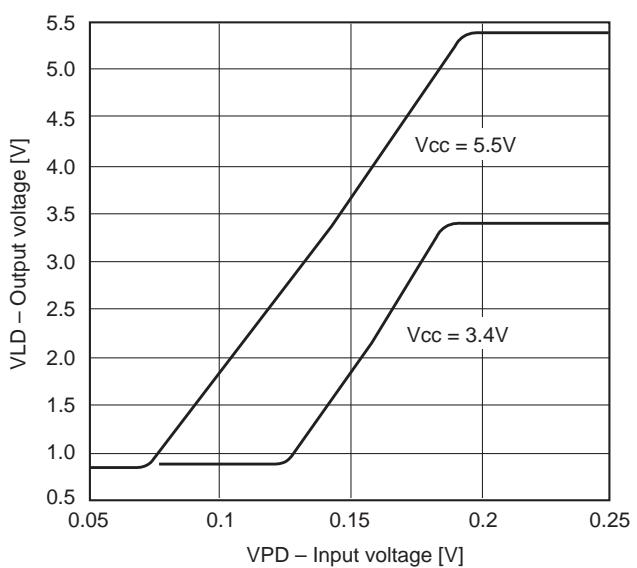
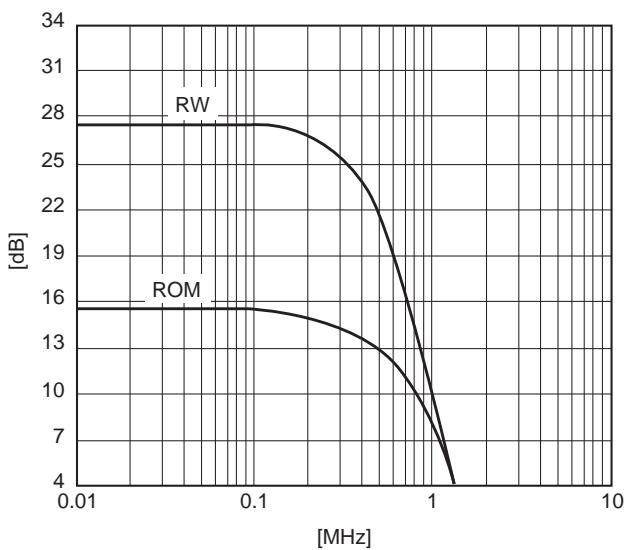


RF DC frequency response



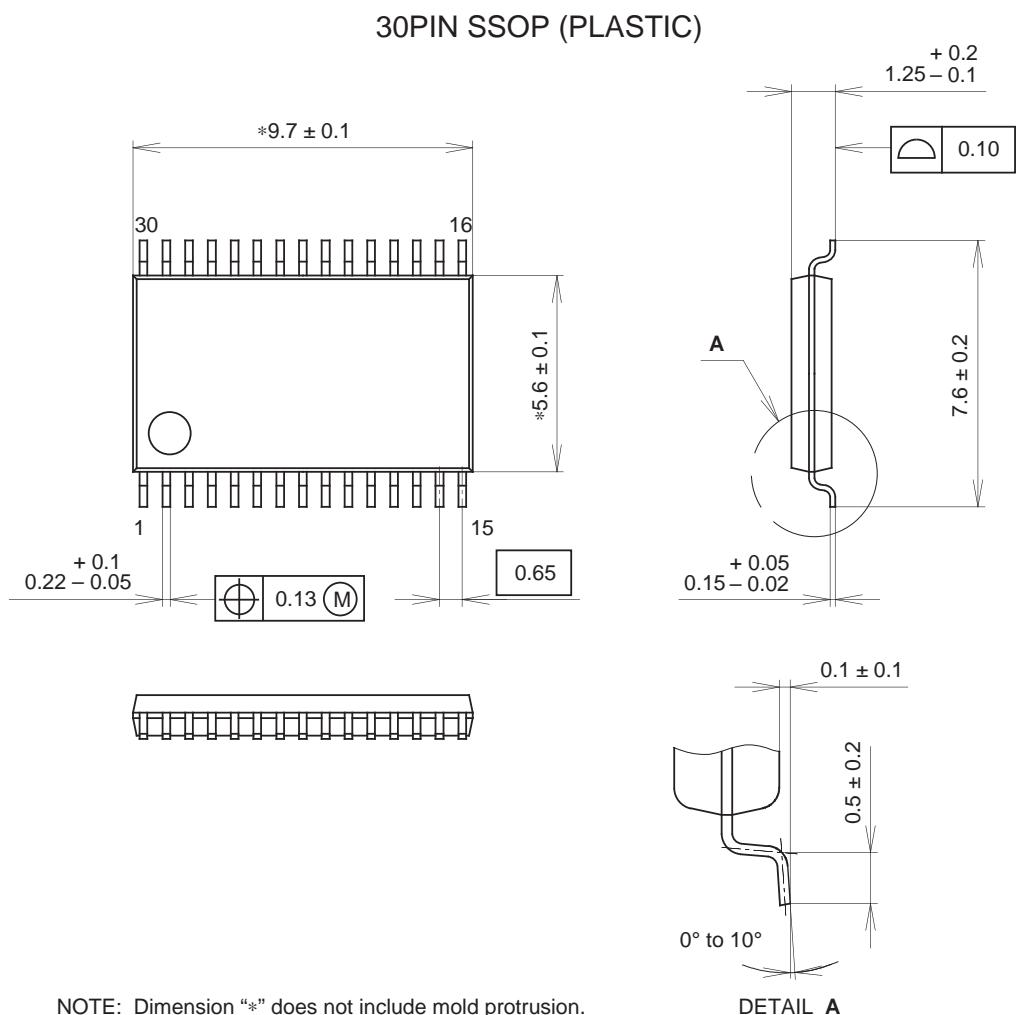
FE frequency response



TE frequency response**APC I/O characteristics****CE frequency response**

Package Outline

Unit: mm



PACKAGE STRUCTURE

SONY CODE	SSOP-30P-L01
EIAJ CODE	SSOP030-P-0056
JEDEC CODE	_____

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER/PALLADIUM PLATING
LEAD MATERIAL	42/COPPER ALLOY
PACKAGE MASS	0.1g

NOTE : PALLADIUM PLATING

This product uses S-PdPPF (Sony Spec.-Palladium Pre-Plated Lead Frame).